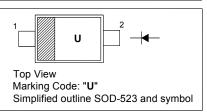
SILICON BAND SWITCHING DIODE

Applications

for band switching in VHF television tuners and surface mount band switching circuits

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current	I _F	100	mA
Junction Temperature	T _J	150	°C
Operating Temperature Range	T _{op}	- 55 to + 125	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Тур.	Max.	Unit
Reverse Current at V _R = 20 V	I _R	-	-	20	nA
Forward Voltage at I _F = 100 mA	V _F	-	-	1	V
Diode Capacitance at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$ at $V_R = 3 \text{ V}$, $f = 1 \text{ MHz}$ at $V_R = 0 \text{ V}$, $f = 100 \text{ MHz}$	Ст	0.65 0.6 -	- - 1	1.4 1.1	pF
Forward Resistance at I_F = 3 mA, f = 100 MHz at I_F = 10 mA, f = 100 MHz	r _f	1 1	-	0.7 0.5	Ω
Series Inductance	L _s	-	0.6	-	nH



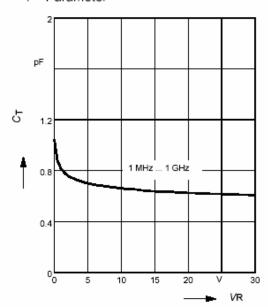




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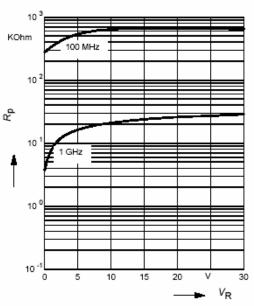
Diode capacitance $C_T = f(V_R)$

f = Parameter



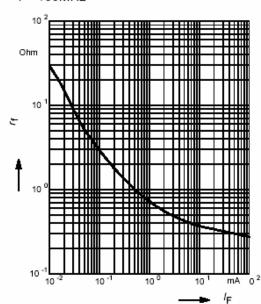
Reverse parallel resistance $R_P = f(V_R)$

f = Parameter



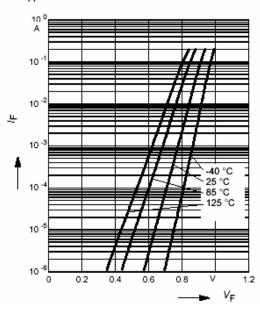
Forward resistance $r_f = f(I_F)$

f = 100MHz



Forward current $I_F = f(V_F)$

 T_A = Parameter





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Dated: 23/11/2006

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523

